

IN THE CLAIMS:

The status of each claim that has been introduced in the above-referenced application is identified in the ensuing listing of the claims. This listing of the claims replaces all previously submitted claims listings.

1. (Currently amended) A method for establishing an electrical contact with at least one semiconductor device, comprising:
establishing an electrical contact between a first member of an electrical connector and a contact
that is in electrical communication with the at least one semiconductor device; and
drawing said the first member toward said the contact.

2. (Currently amended) The method of claim 1, wherein said the drawing is effected in a direction substantially normal to a plane of said the contact.

3. (Currently amended) The method of claim 1, wherein said the drawing is effected in a direction substantially normal to a plane of a substrate upon which said the contact is carried.
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4. (Currently amended) The method of claim 1, wherein said the drawing is effected by positioning a second member of said the electrical connector opposite said the first member.

5. (Currently amended) The method of claim 4, wherein said the drawing is effected by magnetically attracting at least one of said the first member and said the second member toward at least the other of said the first member and said the second member.

6. (Currently amended) The method of claim 4, wherein said the drawing comprises securing said the first and second members to a substrate upon which said the contact is carried.

7. (Currently amended) The method of claim 1, wherein said the drawing comprises magnetically attracting said the first member against said the contact.

8. (Currently amended) A method for stress testing a plurality of semiconductor devices carried upon a common substrate and in communication with common ground and power contacts, comprising:

establishing electrical contact between a first member of an electrical connector and at least one contact of the ground contact and the power contact; and
drawing said the first member toward said the at least one contact.

9. (Currently amended) The method of claim 8, wherein said the drawing is effected in a direction substantially normal to a plane of the substrate.

10. (Withdrawn)

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11. (Currently amended) The method of claim 8, wherein said the drawing comprises positioning a second member of said the electrical connector opposite the substrate from said the first member.

12. (Currently amended) The method of claim 11, wherein at least one of said the first member and said the second member is drawn toward at least the other of said the first member and said the second member.

13. (Currently amended) The method of claim 12, wherein said the drawing comprises magnetically attracting at least one of said the first member and said the second member toward at least the other of said the first member and said the second member.

14. (Currently amended) The method of claim 8, wherein said the drawing comprises magnetically attracting said the first member against said the at least one contact.

15. (Currently amended) The method of claim 8, wherein said the drawing comprises securing at least said the first member in position relative to the substrate.

16. (Currently amended) The method of claim 8, further comprising: electrically connecting another first member of another electrical connector to another of the ground contact and the power contact; and drawing said the another first member toward said the another contact.

17. (Currently amended) The method of claim 16, further comprising: applying a substantially constant amount of current to each semiconductor device of the plurality of semiconductor devices through said the first member and said the another first member.

18. (Currently amended) The method of claim 17, further comprising: heating each of the plurality of semiconductor devices.

19. (Currently amended) The method of claim 18, wherein said the heating comprises cycling a temperature of each of the plurality of semiconductor devices.

20. (Currently amended) The method of claim 18, wherein said the heating comprises varying a temperature of each of the plurality of semiconductor devices.